

Appl. No. 09/650,275
Amtd. dated July 18, 2003
Reply to Office Action of April 24, 2003

PATENT

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

1 1. (Currently Amended) A die seal structure for a semiconductor die having
2 a substrate comprising:
3 an elongate region electrically isolated from the remainder of the substrate
4 extending around a major portion of the periphery of the substrate and having a gap between
5 ends of the elongate region along a minor portion of the periphery; and
6 a conductive seal ring extending around the entire periphery of the die in direct contact
7 with the die [[throughout]] along said elongate region [[in direct contact with]] and in direct
8 contact with said gap to provide a limited electrical connection between the ring and the
9 substrate only at said gap.

Please cancel claims 9-13.

1 14. (Currently Amended) A die seal structure for a semiconductor die having
2 a substrate of a first conductivity type, comprising:
3 an elongate well region of a second conductivity type opposite from the first
4 conductivity type extending around a major portion of the periphery of the substrate and having a
5 gap between the ends of the elongate region along a minor portion of the periphery; and
6 a conductive seal ring extending around the entire periphery of the die in direct contact
7 with the die [[throughout]] along said elongate well region and in direct contact with said gap to
8 provide a limited electrical connection between the ring and the substrate of said first
9 conductivity type only at said gap.

1 18. (Currently Amended) A semiconductor device comprising:
2 C2 a. a die including a substrate;
3 b. a die seal structure on the substrate, the structure comprising:

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- 4 an elongate region electrically isolated from the remainder of the substrate
5 extending around a major portion of the periphery of the substrate and having a gap between
6 ends of the elongate region along a minor portion of the periphery; and
C2 7 a conductive seal ring extending around the entire periphery of the die in direct contact
8 with the die [[throughout]] along said elongate region and in direct contact with said gap to
9 provide a limited electrical connection between the ring and the substrate only at said gap.
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